

**Please delete the present Abstract of the Disclosure.**

**Please add the following new Abstract of the Disclosure:**

A thin-film semiconductor device is provided including a plurality of thin-film transistors (TFT) having different driving voltages formed on an glass substrate, wherein a gate ~~electrode~~ insulator electric field at each of the driving voltages of the plurality of thin-film transistors is in a range of about 1MV/cm to 2MV/cm, and a drain concentration of p-type thin-film transistors (TFT) is in a range of about 3E+19/cm<sup>3</sup> to 1E+20/cm<sup>3</sup>.